

SANYO

No.1799D

2SC3576

NPN Epitaxial Planar Silicon Transistor

High h_{FE} , Low-Frequency
General-Purpose Amp Applications**Applications**

- LF general-purpose amplifiers, various drivers, muting circuit

Features

- Adoption of FBET process
- High DC current gain ($h_{FE}=800$ to 3200).
- Low collector-to-emitter saturation voltage ($V_{CE(sat)} \leq 0.5V$).
- High V_{EBO} ($V_{EBO} \geq 15V$).

Absolute Maximum Ratings at $T_a=25^\circ C$

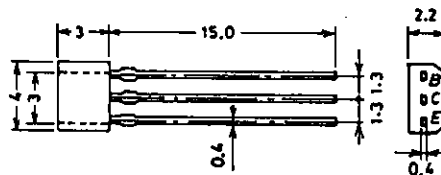
			unit
Collector to Base Voltage	V_{CBO}	30	V
Collector to Emitter Voltage	V_{CEO}	25	V
Emitter to Base Current	V_{EBO}	15	V
Collector Current	I_C	300	mA
Collector Current(Pulse)	I_{CP}	500	mA
Base Current	I_B	60	mA
Collector Dissipation	P_C	300	mW
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to +150	$^\circ C$

Electrical Characteristics at $T_a=25^\circ C$

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=20V, I_E=0$			0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=10V, I_C=0$			0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=5V, I_C=10mA$	800	1500	3200	
Gain-Bandwidth Product	f_T	$V_{CE}=10V, I_C=10mA$		250		MHz
Output Capacitance	c_{ob}	$V_{CB}=10V, f=1MHz$		2.7		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=200mA, I_B=4mA$		0.12	0.5	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C=200mA, I_B=4mA$		0.85	1.2	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	30			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1mA, R_{BE}=\infty$	25			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	15			V

Package Dimensions 2033

(unit: mm)



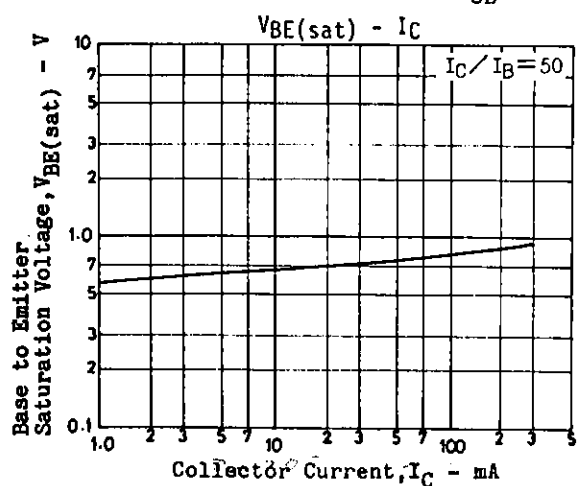
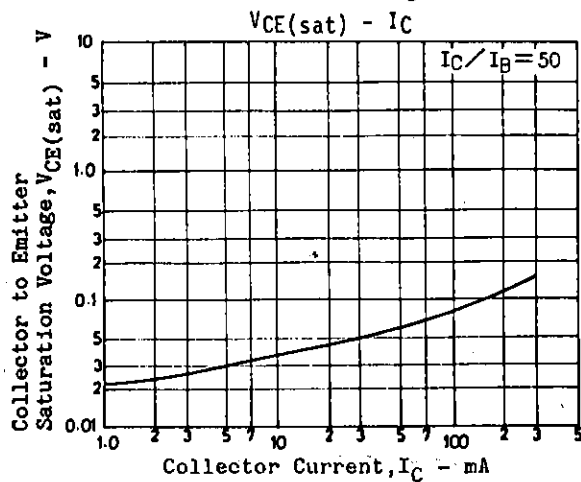
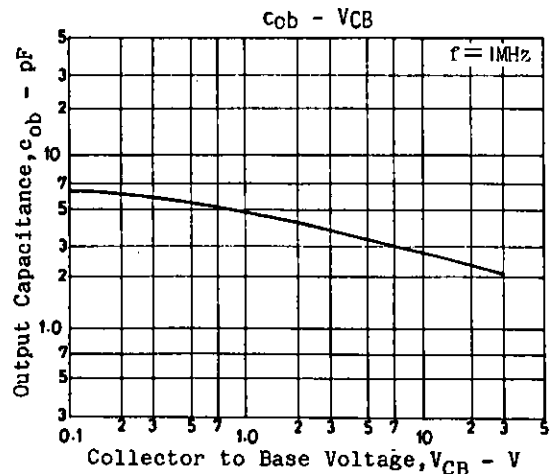
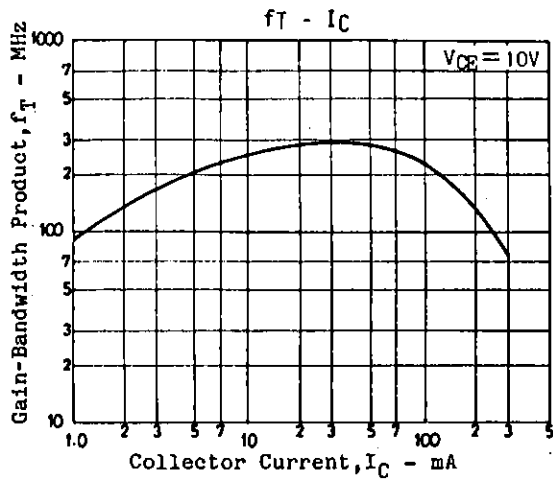
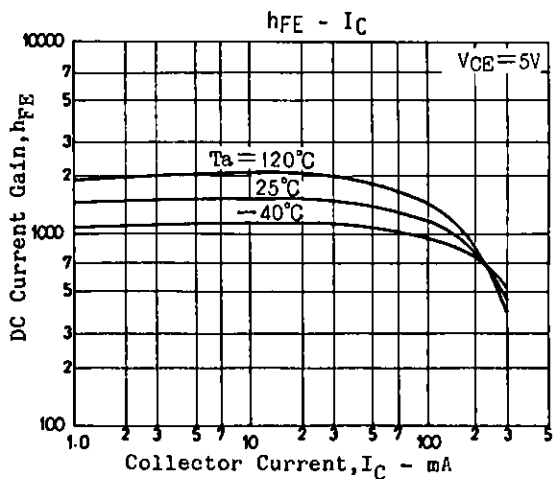
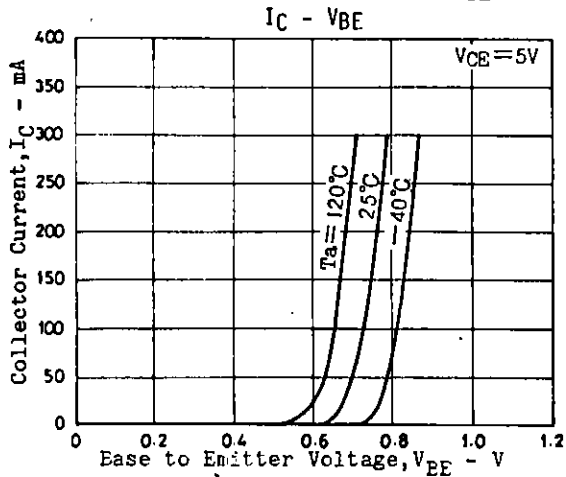
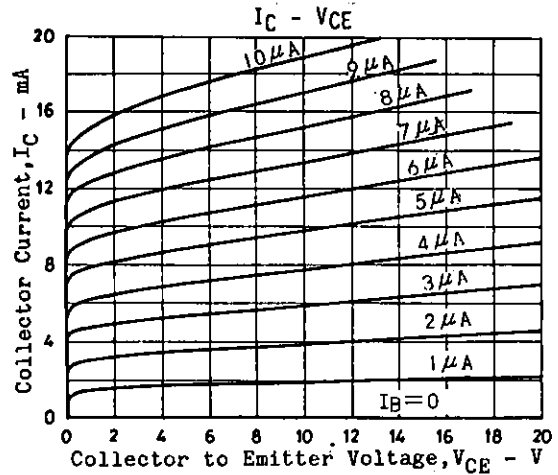
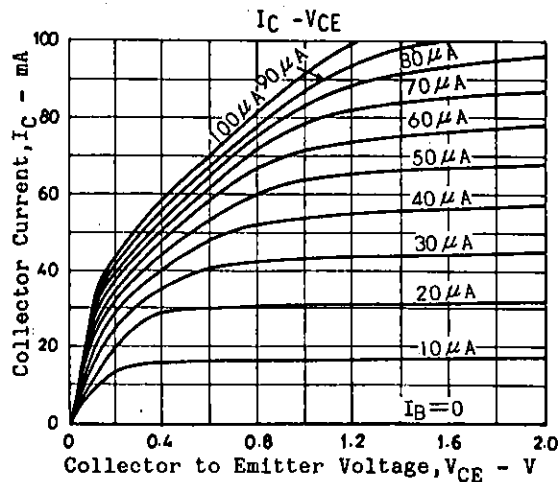
B: Base
C: Collector
E: Emitter

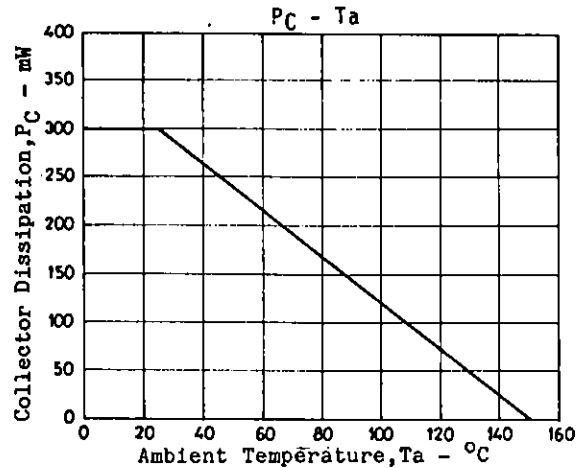
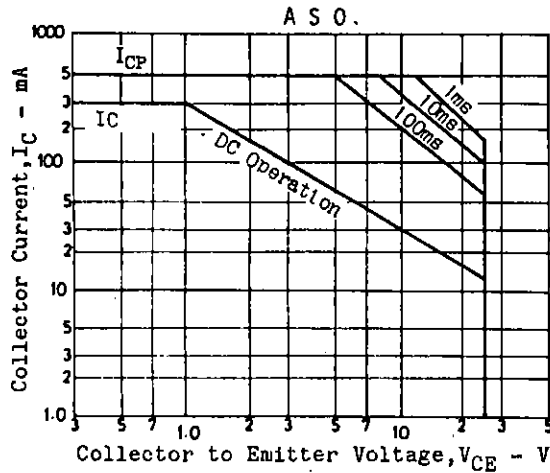
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